

Contents

Materials

- Design properties of polycrystalline silicon. 817
T. I. Kamins (Palo Alto, CA, U.S.A.)
- Porous silicon morphologies and formation mechanism. 825
R. L. Smith, S. D. Collins (Davis, CA, U.S.A.) and S.-F. Chuang (Cambridge, MA, U.S.A.)
- Thick films of silicon nitride 830
R. L. Smith and S. D. Collins (Davis, CA, U.S.A.)
- Investigations of porous silicon for vapor sensing. 835
R. C. Anderson, R. S. Muller and C. W. Tobias (Berkeley, CA, U.S.A.)
- SOI structure pressure transducer formed by oxidized porous silicon. 840
Ganming Zhao, Yiping Huang and Minhang Bao (Shanghai, China)
- Creep of sensor's elastic elements: metals versus non-metals. 844
K. Bethe, D. Baumgarten and J. Frank (Braunschweig, F.R.G.)
- Modeling of thermal and mechanical stresses in silicon microstructures 850
F. Pourahmadi, P. Barth and K. Petersen (Fremont, CA, U.S.A.)
- Thermophysical properties of low-residual stress, silicon-rich, LPCVD silicon nitride films. . . 856
C. H. Mastrangelo, Y.-C. Tai and R. S. Muller (Berkeley, CA, U.S.A.)
- Plastic deformation of highly doped silicon 861
F. Maseeh and S. D. Senturia (Cambridge, MA, U.S.A.)
- Residual stress and mechanical properties of boron-doped p^+ -silicon films 866
X. Ding, W. H. Ko and J. M. Mansour (Cleveland, OH, U.S.A.)
- Fracture toughness characterization of brittle thin films 872
L. S. Fan, R. T. Howe and R. S. Muller (Berkeley, CA, U.S.A.)
- New aspects of giant exciton Faraday rotation in $Cd_{1-x}Mn_xTe$ semimagnetic compound: fundamentals and applications. 875
D. A. Aksionov, V. I. Konov, P. I. Nikitin, A. M. Prokhorov, A. I. Savchuk, A. V. Savitski and K. S. Ulyanitski (Moscow, U.S.S.R.)
- A piezopolymer finger pulse and breathing wave sensor 879
Yuquan Chen, Liren Wang (Hangzhou, China) and W. H. Ko (Cleveland, OH, U.S.A.)
- PVDF film multifunction sensors 883
Wang Shu-Duo (Beijing, China)
- A PVDF film sensor for material identification 886
Guowei Gao, Zicheng Wang and Rui Gao (Beijing, China)

Technology

- A LOCOS process for an electrostatic microfabricated motor. 893
L. S. Tavrow, S. F. Bart, J. H. Lang and M. F. Schlecht (Cambridge, MA, U.S.A.)
- Vertically structured silicon membranes by electrochemical etching 899
R. Huster and A. Stoffel (Furtwangen, F.R.G.)
- A sub-micron particle filter in silicon. 904
G. Kittilsland, G. Stemme and B. Nördén (Göteborg, Sweden)
- How to liberate integrated sensors from encapsulation stress 908
B. Hälg and R. S. Popovic (Zug, Switzerland)

Electrochemical deposition of conducting polymers onto electronic substrates for sensor applications	911
P. N. Bartlett, J. W. Gardner and R. G. Whitaker (Coventry, U.K.)	
Process alternatives and scaling limits for high-density silicon tactile imagers.	915
K. Suzuki (Kanagawa, Japan), K. Najafi and K. D. Wise (Ann Arbor, MI, U.S.A.)	
Silicon fusion bonding for fabrication of sensors, actuators and microstructures	919
P. W. Barth (Fremont, CA, U.S.A.)	
Wafer bonding: investigation and <i>in situ</i> observation of the bond process	927
C. Harendt, H.-G. Graf, E. Penteker and B. Höfflinger (Stuttgart, F.R.G.)	
Low-temperature silicon-to-silicon anodic bonding with intermediate low melting point glass	931
M. Esashi, A. Nakano, S. Shoji and H. Hebiguchi (Sendai, Japan)	
Fusing silicon wafers with low melting temperature glass.	935
L. A. Field and R. S. Muller (Berkeley, CA, U.S.A.)	
The mechanism of field-assisted silicon-glass bonding	939
Y. Kanda, K. Matsuda, C. Murayama and J. Sugaya (Hamamatsu, Japan)	
An implantable pressure sensor for use in cardiology	944
B. Puers, A. Van den Bossche, E. Peeters and W. Sansen (Heverlee, Belgium)	
Individual and mass operation of biological cells using micromechanical silicon devices.	948
K. Sato, Y. Kawamura, S. Tanaka, K. Uchida and H. Kohida (Tokyo, Japan)	
Stable operation of Topografiner in the atmosphere by use of charge injection current in an insulating liquid	954
H. Adachi, A. Suzuki, T. Onodera, K. Suzuki (Hokkaido, Japan) and K. Mukasa (Sapporo, Japan)	
Pressure sensor using polycrystalline germanium films prepared by plasma-assisted chemical vapour deposition	958
K. Kamimura, N. Kimura, Y. Onuma (Nagano-shi, Japan) and T. Homma (Nagano, Japan)	
A new silicon micromachining method using SOI/SDB technology	961
Shi-Ji Lu, Zheng Zheng and Qin-Yi Tong (Nanjing, China)	
A planar process for microfabrication of a scanning tunneling microscope	964
S. Akamine, T. R. Albrecht, M. J. Zdeblick and C. F. Quate (Stanford, CA, U.S.A.)	
Micromachining of quartz and its application to an acceleration sensor	971
J. S. Danel, F. Michel and G. Delapierre (Grenoble, France)	
Batch processing of laterally mobile structures in single-crystalline silicon	978
U. Lindberg, B. Hök, L. Tenerz, J. Tirén and Y. Bäcklund (Uppsala, Sweden)	
PECVD diamond films for use in silicon microstructures.	982
J. A. Herb, M. G. Peters (Menlo Park, CA, U.S.A.), S. C. Terry and J. H. Jerman (Milpitas, CA, U.S.A.)	
The fabrication and use of micromachined corrugated silicon diaphragms.	988
J. H. Jerman (Milpitas, CA, U.S.A.)	
The compatibility of PECVD diamond in the design and fabrication of a self-aligned rigid suspended plate.	993
R. W. Bower (Davis, CA, U.S.A.)	
Flexible miniature ribbon cables for long-term connection to implantable sensors	999
J. F. Hetke, K. Najafi and K. D. Wise (Ann Arbor, MI, U.S.A.)	
'SIMOX' (separation by ion implantation of oxygen): a technology for high-temperature silicon sensors.	1003
B. Diem, R. Truche, S. Viollet-Bosson and G. Delapierre (Grenoble, France)	

Three-dimensional micromachining of silicon pressure sensor integrating resonant strain gauge on diaphragm	1007
K. Ikeda, H. Kuwayama, T. Kobayashi, T. Watanabe, T. Nishikawa, T. Yoshida and K. Harada (Tokyo, Japan)	
Laser-assisted direct writing of strain sensitive silicon resistors	1011
J. Lenkkeri and S. Leppävuori (Oulu, Finland)	
Realization of a temperature transducer by a standard polysilicon process	1015
O. Zucker, W. Langheinrich, M. Hierholzer and J. Meyer (Darmstadt, F.R.G.)	
Field oxide microbridges, cantilever beams, coils and suspended membranes in SACMOS technology	1019
D. Moser, M. Parameswaran and H. Baltes (Zurich, Switzerland)	
New suspended gate FET technology for physical deposition of chemically sensitive layers . .	1023
H. Lorenz, M. Peschke, H. Riess, J. Janata and I. Eisele (Neubiberg, F.R.G.)	
Compatibility of zinc oxide with silicon IC processing	1027
M. J. Vellekoop, C. C. G. Visser, P. M. Sarro and A. Venema (Delft, The Netherlands)	
NH ₄ OH-based etchants for silicon micromachining	1031
U. Schnakenberg, W. Benecke and B. Löchel (Berlin, F.R.G.)	
Compensation structures for convex corner micromachining in silicon	1036
B. Puers and W. Sansen (Heverlee, Belgium)	
Edges and corners of multilayer dynamic microstructures	1042
Lj. Ristić, A. C. Dhaded, K. Chau and W. Allegretto (Edmonton, Alta., Canada)	
Absolute pressure sensors by air-tight electrical feedthrough structure	1048
M. Esashi, Y. Matsumoto and S. Shoji (Sendai, Japan)	
Investigations on free-standing polysilicon beams in view of their application as transducers .	1053
C. Linder and N. F. de Rooij (Neuchâtel, Switzerland)	
Mechanical design issues in laterally-driven microstructures	1060
A. P. Pisano and Y.-H. Cho (Berkeley, CA, U.S.A.)	
Mechanical decoupling of monolithic pressure sensors in small plastic encapsulations	1065
W. Germer and G. Kowalski (Hamburg, F.R.G.)	
Silicon pressure transducer arrays for blood-pressure measurement	1070
S. Terry (Milpitas, CA, U.S.A.), J. S. Eckerle, R. D. Kornbluh, T. Low and C. M. Ablow (Menlo Park, CA, U.S.A.)	
Ceramic sensor technology for the measurement of mechanical quantities at high temperature	1080
J. Knapp, G. Andreae and D. Petersohn (Berlin, F.R.G.)	
Fiber Sensors	
Silicon-based integrated optics technology for optical sensor applications	1087
S. Valette, S. Renard, J. P. Jadot, P. Gidon and C. Erbeia (Grenoble, France)	
Realization of a miniaturized optical sensor for biomedical applications	1092
P. Poscio, C. Depeursinge (Ecublens, Switzerland), G. Voirin, B. Sheja and O. Parriaux (Neuchâtel, Switzerland)	
Optical fiber transducers using Fabry-Perot resonators	1097
F. Maystre and R. Dändliker (Neuchâtel, Switzerland)	
Sensitivity enhancement of evanescent wave integrated optic transducers	1102
O. Parriaux, G. Kotrotsios and V. Neuman (Neuchâtel, Switzerland)	
The optical properties of curing epoxies and applications to the fiber-optic epoxy cure sensor	1107
M. A. Afromowitz and K.-Y. Lam (Seattle, WA, U.S.A.)	

Fibre optic sensors for the characterization of particle size and flow velocity	1111
R. J. G. Carr (Porton Down, U.K.)	
A hybrid fiber-optic—piezoelectric multistable set-up for digital positioning of a piezoelectric translator	1118
N. Fürstenau, W. Schmidt and C. Watts (Braunschweig, F.R.G.)	
Integrated optoelectronic circuits using metal—semiconductor—metal photodetectors	1124
H. Pohjonen and M. Andersson (Espoo, Finland)	
Hybrid fiber-optic/micromechanical frequency encoding displacement sensor	1128
G. Grosch (Munich, F.R.G.)	
Temperature determination of high-temperature gas by fiber-optic infrared spectroscopy . . .	1132
M. Maeda and M. Katsuyama (Tokyo, Japan)	
Plasmon wave versus dielectric waveguiding for surface wave sensing	1137
O. Parriaux and G. Voirin (Neuchâtel, Switzerland)	
Optical fibre device for chemical sensing based on surface plasmon excitation	1142
F. Villuendas and J. Pelayo (Zaragoza, Spain)	
Photothermal excitation of resonant structures in fibre optic sensors: application of computer modelling techniques	1146
K. T. V. Grattan (London, U.K.)	
An optical method for detecting anesthetics and other lipid-soluble compounds	1150
S. Merlo, P. Yager and L. W. Burgess (Seattle, WA, U.S.A.)	
Lateral optical coupling between integrated ion-exchanged waveguides in glass and a-Si _{1-x} Ge _x :H photodetectors	1155
P. P. Deimel, B. B. Heimhofer, G. Müller and M. Königer (Munich, F.R.G.)	
Formation and power distribution properties of an upside down taper lens at the end of an optical fiber	1158
L. B. Yuan and R. L. Shou (Harbin, China)	
Author Index	1163
Subject Index	1167

